

Device Modeling Report

COMPONENTS:BIPOlar JUNCTION TRANSISTOR
PART NUMBER:2SB906
MANUFACTURER: TOSHIBA

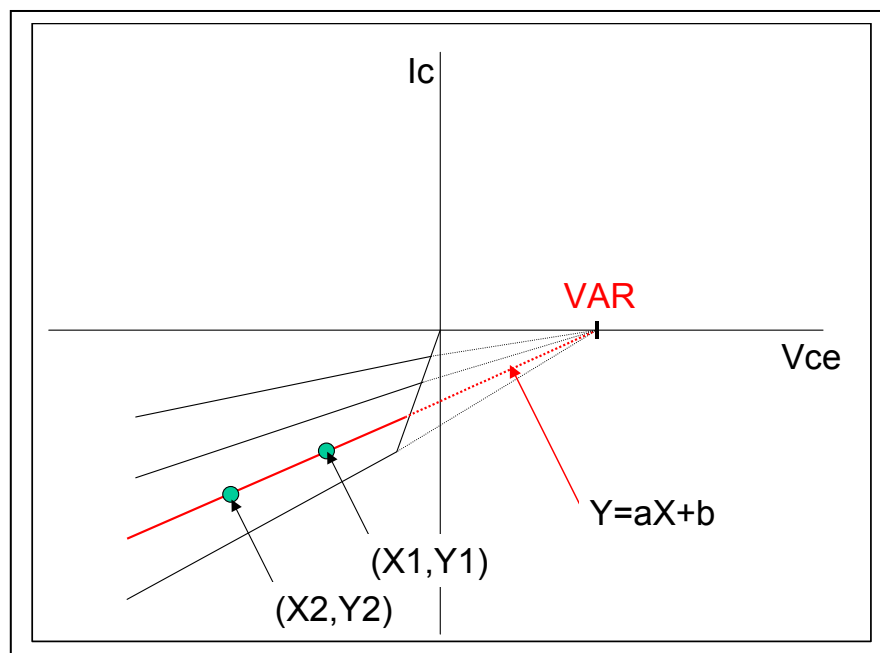
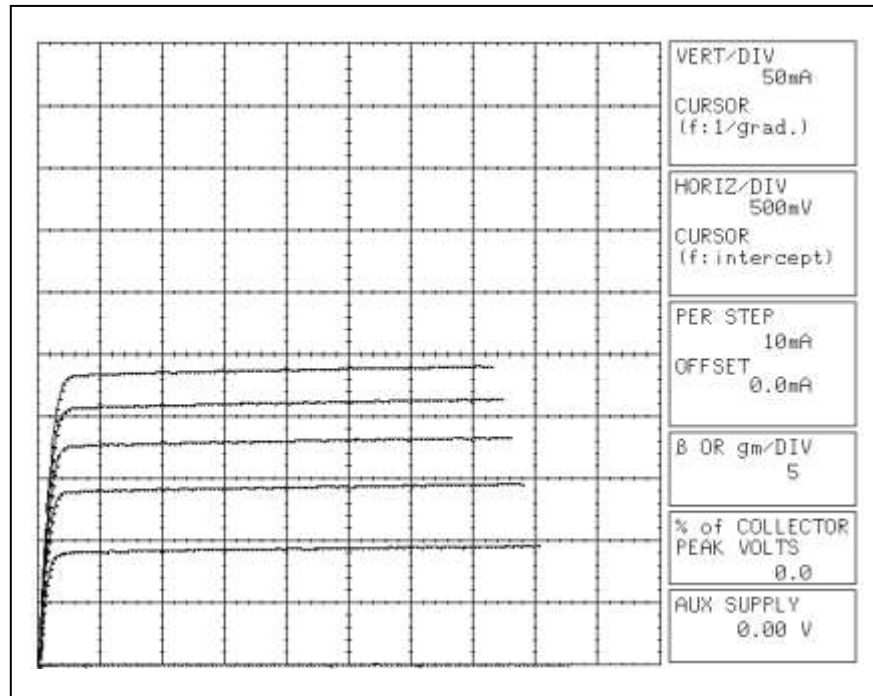


Bee Technologies Inc.

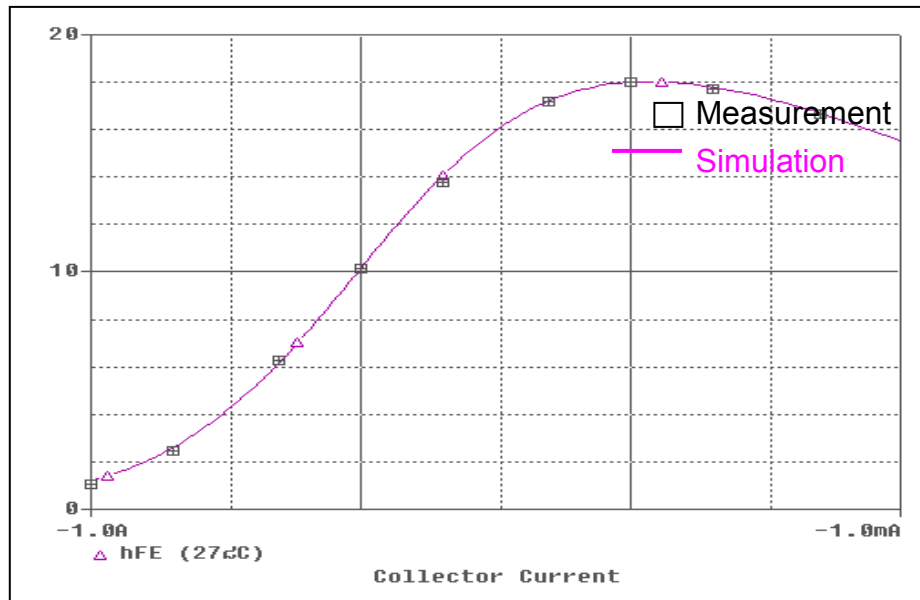
Pspice model parameter	Model description
IS	Saturation Current
BF	Ideal Maximum Forward Beta
NF	Forward Current Emission Coefficient
VAF	Forward Early Voltage
IKF	Forward Beta Roll-off Knee Current
ISE	Non-ideal Base-Emitter Diode Saturation Current
NE	Non-ideal Base-Emitter Diode Emission Coefficient
BR	Ideal Maximum Reverse Beta
NR	Reverse Emission Coefficient
VAR	Reverse Early Voltage
IKR	Reverse Beta Roll-off Knee Current
ISC	Non-ideal Base-Collector Diode Saturation Current
NC	Non-ideal Base-Collector Diode Emission Coefficient
NK	Forward Beta Roll-off Slope Exponent
RE	Emitter Resistance
RB	Base Resistance
RC	Series Collector Resistance
CJE	Zero-bias Emitter-Base Junction Capacitance
VJE	Emitter-Base Junction Potential
MJE	Emitter-Base Junction Grading Coefficient
CJC	Zero-bias Collector-Base Junction Capacitance
VJC	Collector-base Junction Potential
MJC	Collector-base Junction Grading Coefficient
FC	Coefficient for Onset of Forward-bias Depletion Capacitance
TF	Forward Transit Time
XTF	Coefficient for TF Dependency on Vce
VTF	Voltage for TF Dependency on Vce
ITF	Current for TF Dependency on Ic
PTF	Excess Phase at $f=1/2\pi \cdot TF$
TR	Reverse Transit Time
EG	Activation Energy
XTB	Forward Beta Temperature Coefficient
XTI	Temperature Coefficient for IS

Reverse Characteristic

Reverse Early Voltage Characteristic

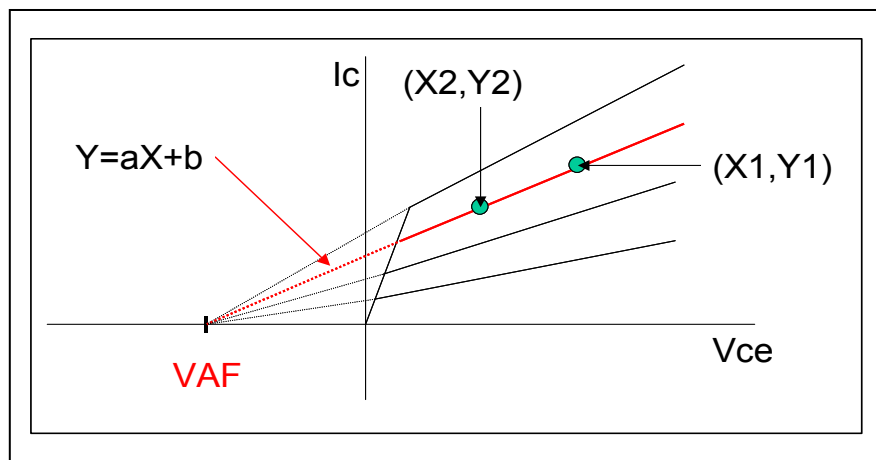
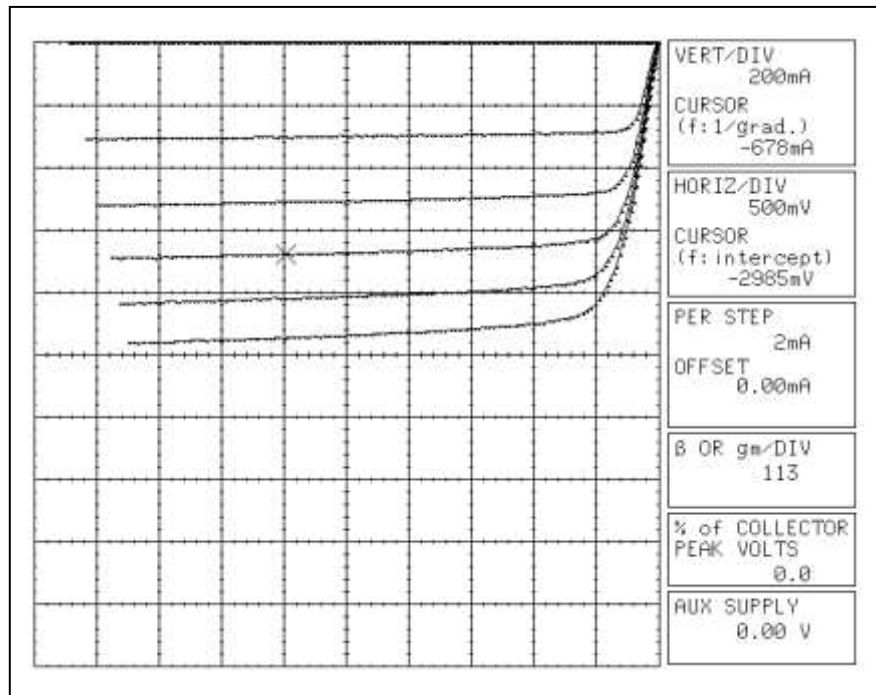


Reverse DC Beta Characteristic (I_e vs. h_{FE})

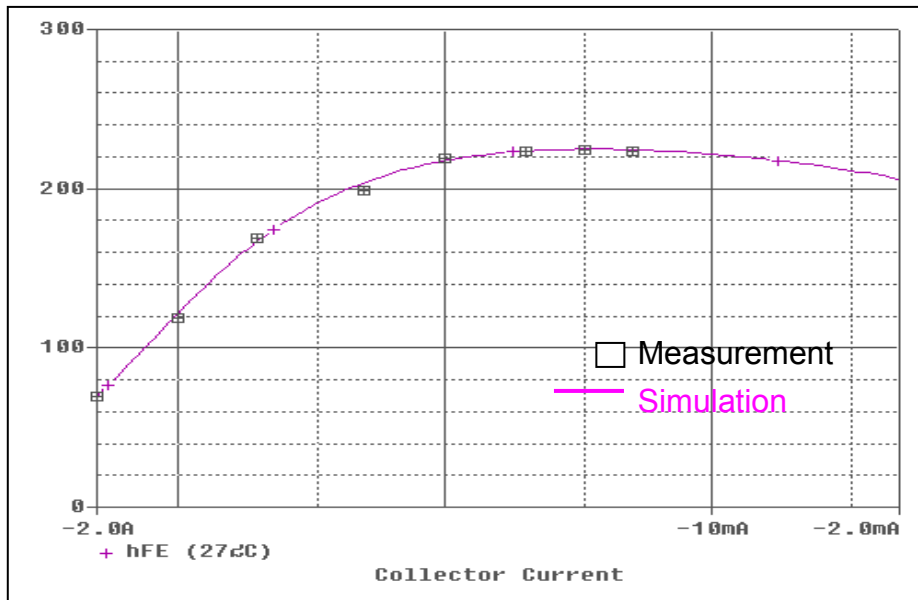


Forward Characteristic

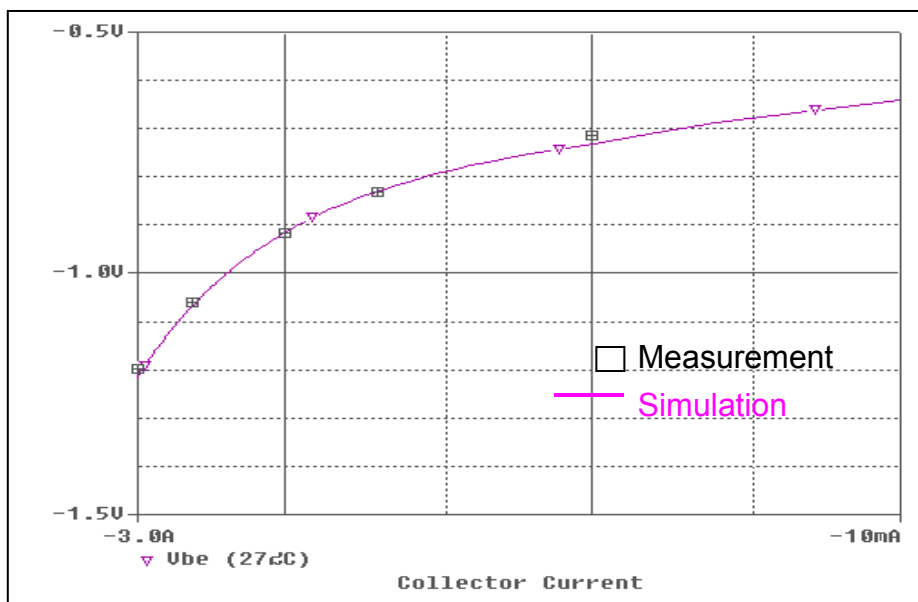
Forward Early Voltage Characteristic



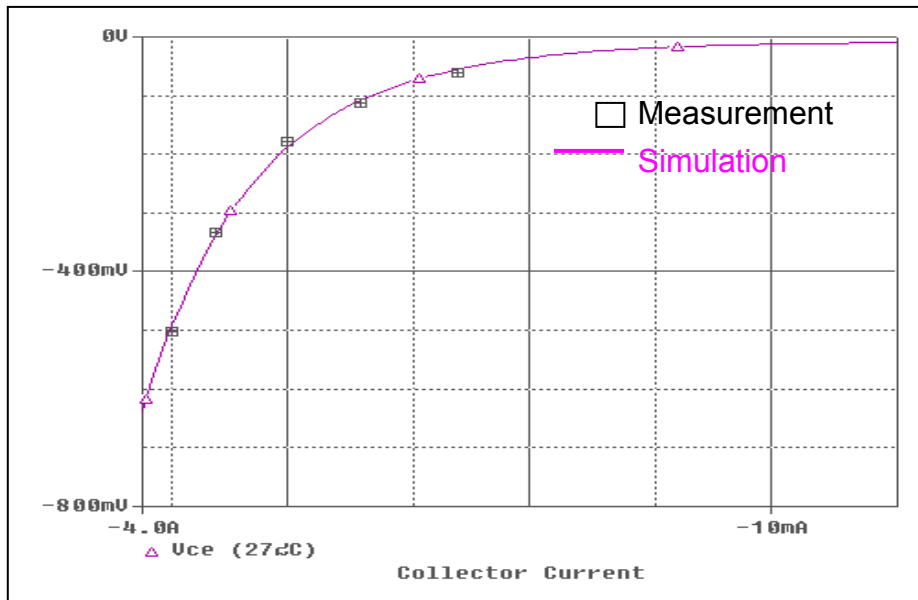
Forward DC Beta Characteristic



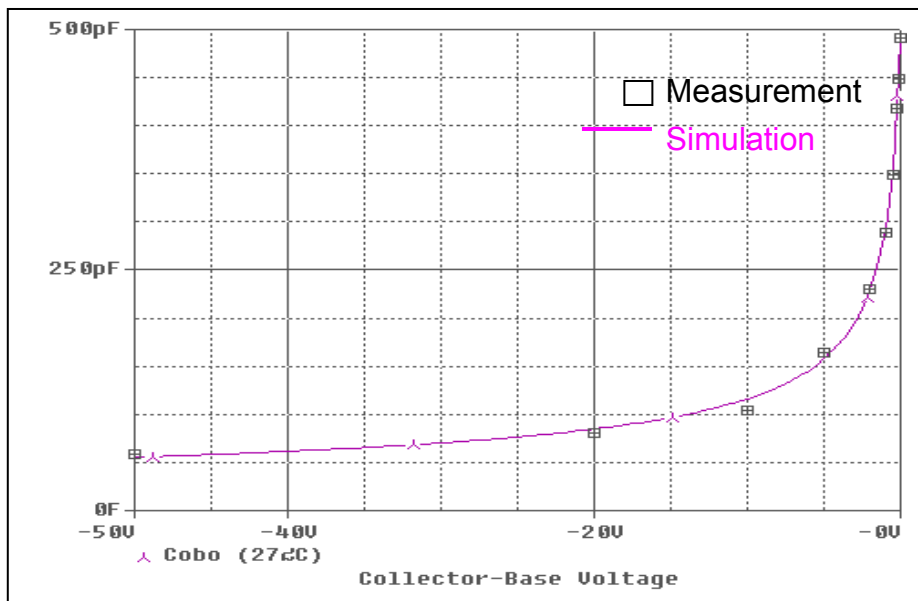
Vbe(sat) Voltage Characteristic



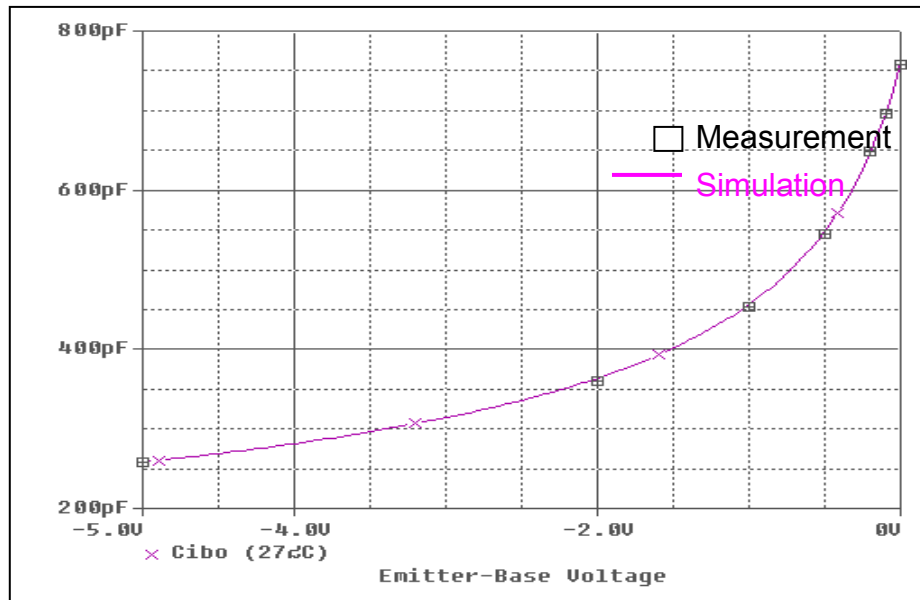
Vce(sat) Voltage Characteristic



C-B Capacitance Characteristic

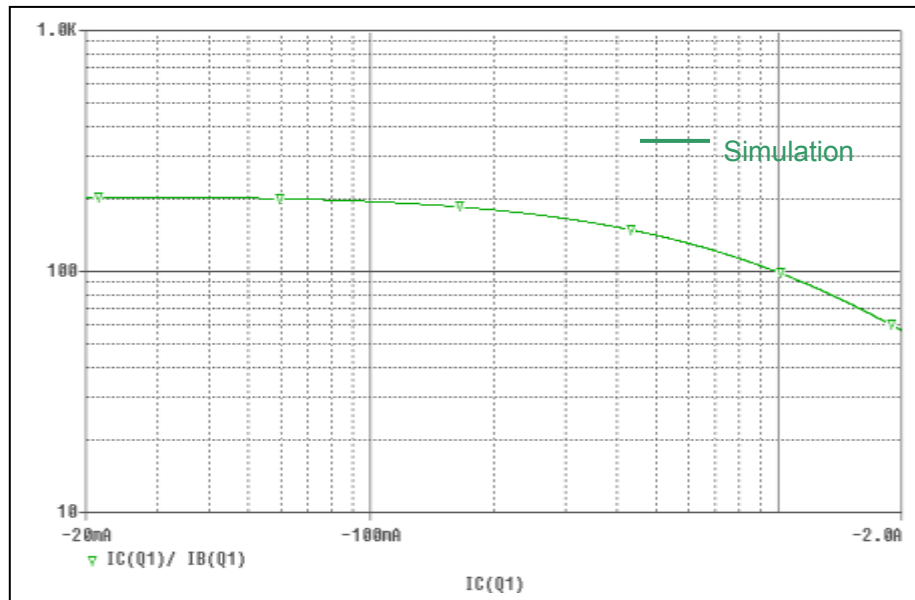


E-B Capacitance Characteristic

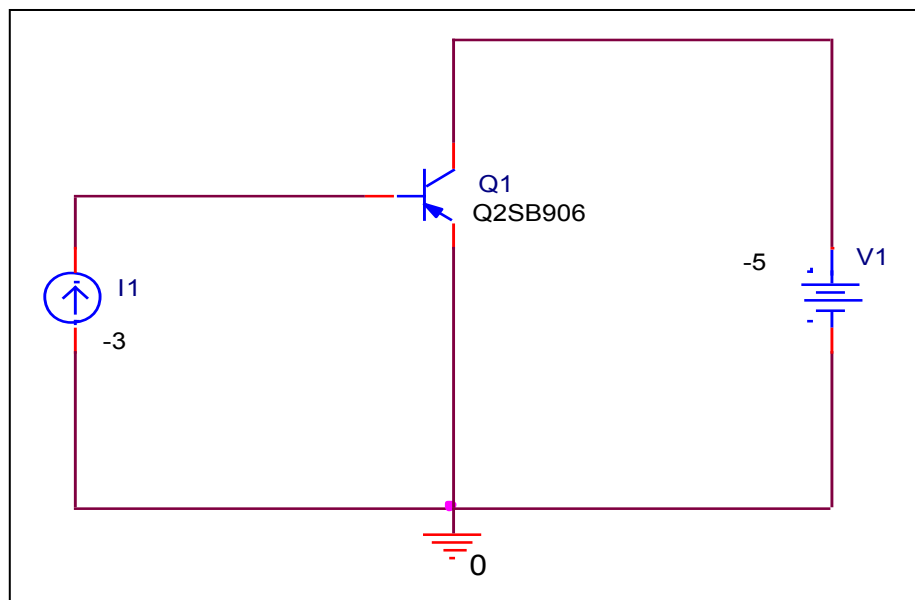


BJT Ic-hFE Characteristics

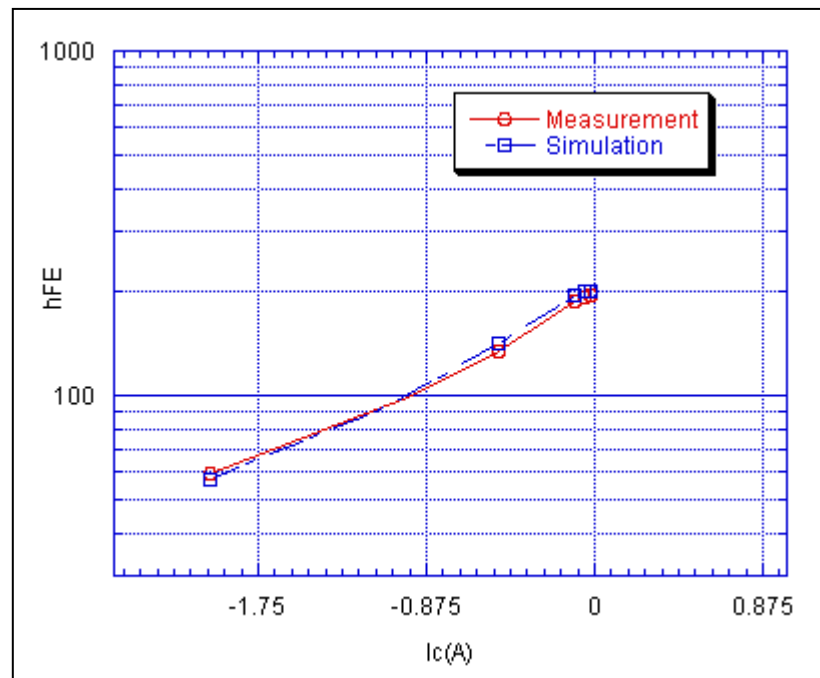
Circuit simulation result



Evaluation circuit



Comparison graph

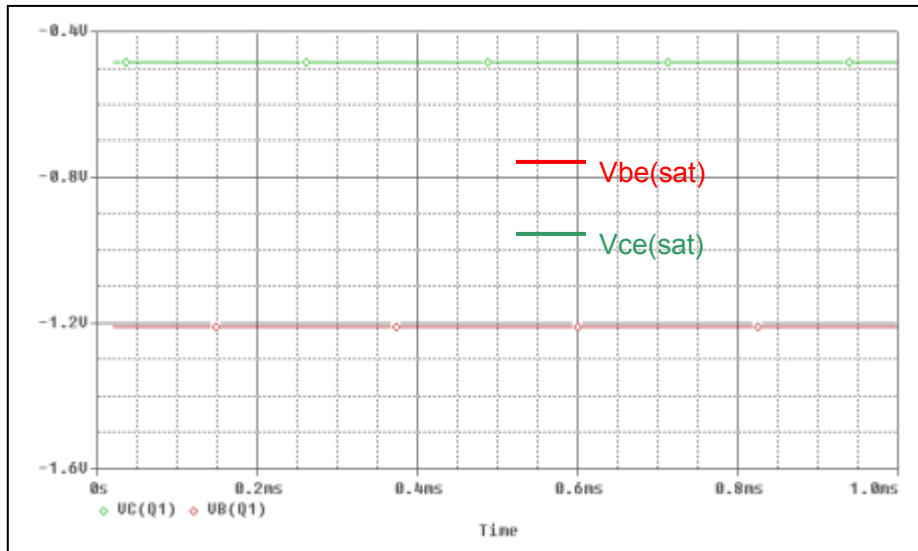


Comparison Table

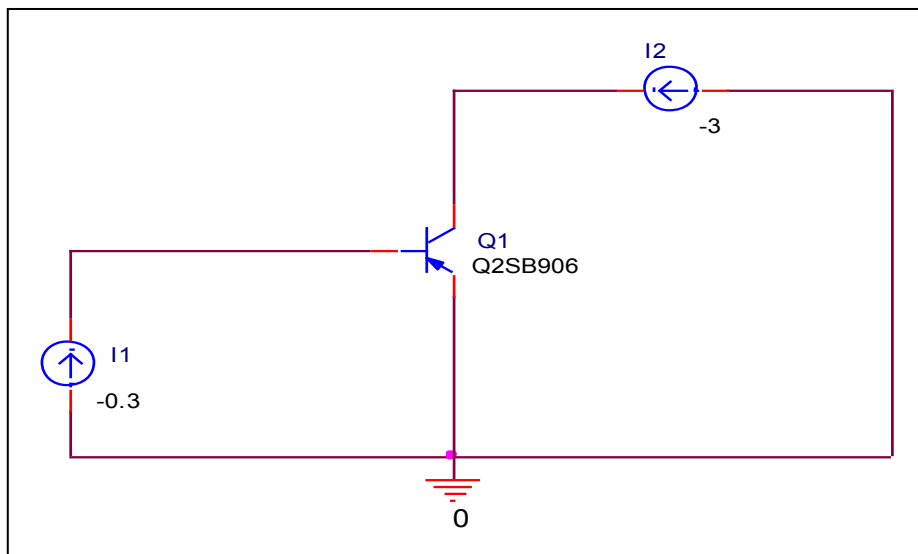
$I_c(A)$	h_{FE}		%Error
	Measurement	Simulation	
-0.02	195.12	201.475	3.257
-0.03	196.08	202.221	3.132
-0.05	194.17	201.229	3.635
-0.1	187.97	195.028	3.755
-0.2	172.71	180.373	4.437
-1	97.466	100.382	2.992
-2	59.701	58.079	-2.717

BJT Vce(sat) voltage& Vbe(sat) voltage Characteristics

Circuit simulation result



Evaluation circuit

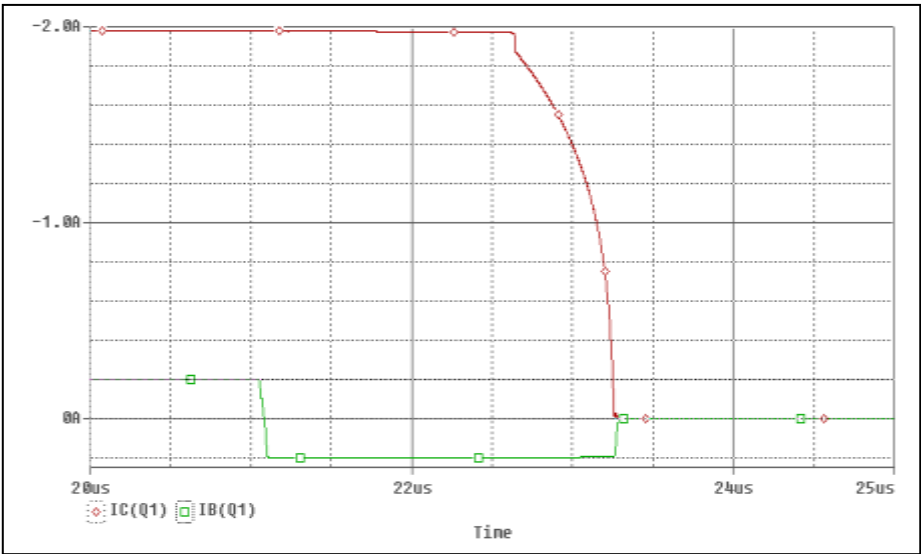


Comparison Table

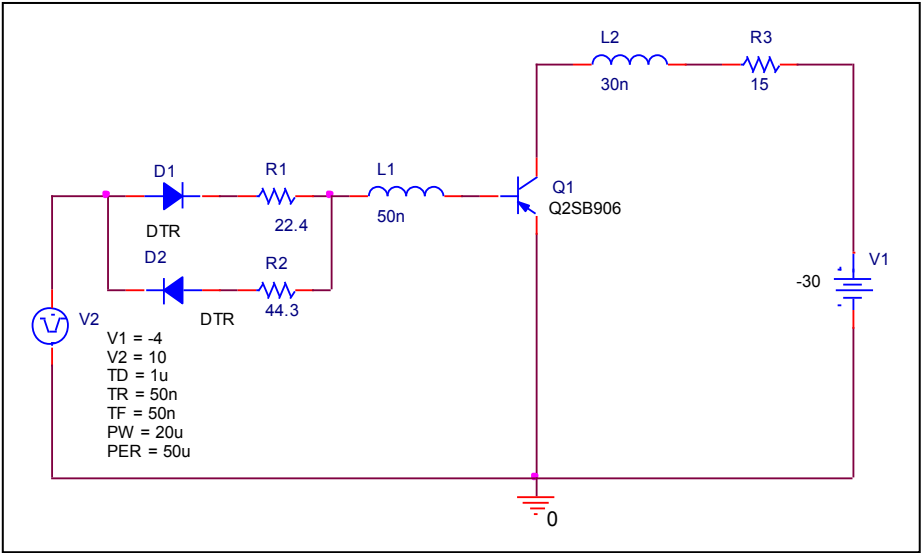
Ic=-3A,Ib=-0.3A	Measurement	Simulation	%Error
Vce(sat) (V)	-0.5	-0.483892	3.222
Vbe(sat) (V)	-1.196	-1.2102	-1.187

BJT Switching Time Characteristic

Circuit simulation result



Evaluation circuit

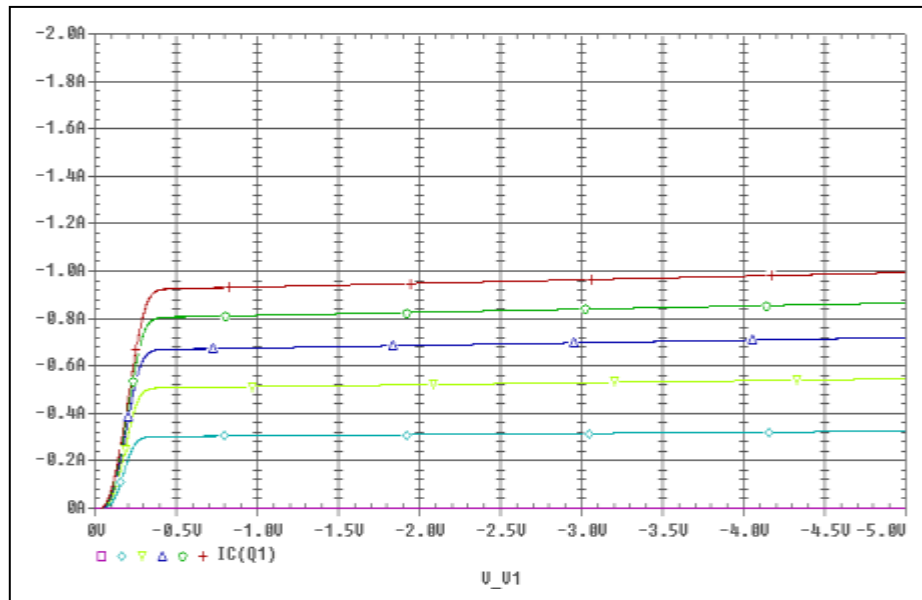


Comparison Table

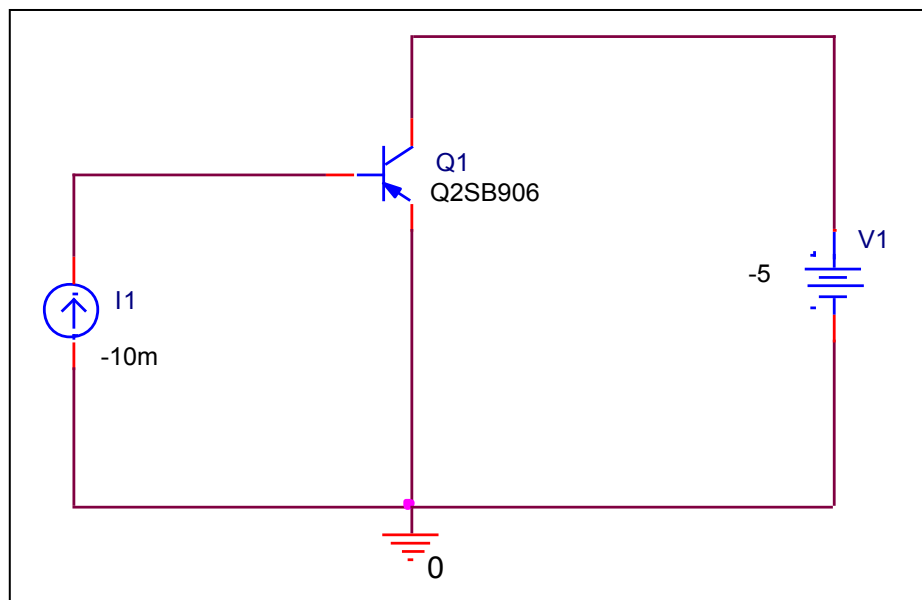
$-I_{B1}=I_{B2}=0.2A,$ $V_{CC}=-30V,R_L=15\Omega$	Measurement	Simulation	%Error
t_f (us)	0.5	0.516393	-3.279
t_s (us)	1.7	1.6799	1.182

BJT Output Characteristic

Circuit simulation result



Evaluation circuit



Reference

